VSSOP20-P-0030-0.50

Weight: 0.03 g (typ.)

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MET374AFK

Octal D-Type Flip-Flop with 3-State Output

The TC7MET374AFK is an advanced high speed CMOS octal flip-flop with 3-state output fabricated with silicon gate $\rm C^2MOS$ technology.

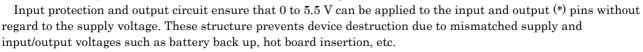
It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

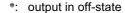
This 8-bit D-type flip-flop is controlled by a clock input (CK) and a output enable input (\overline{OE}) .

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

The input voltage are compatible with TTL output voltage.

This device may be used as a level converter for interfacing $3.3\ V$ to $5\ V$ system.







- High speed: $f_{max} = 140 \text{ MHz}$ (typ.) (VCC = 5 V)
- Low power dissipation: $ICC = 4 \mu A \text{ (max) (Ta} = 25 \text{°C)}$
- Compatible with TTL outputs: V_{IL} = 0.8 V (max) $V_{IH} = 2.0 \ V \ (min)$
- Power down protection is provided on all inputs and outputs.
- Balanced propagation delays: $t_pLH \simeq t_pHL$
- Low noise: VOLP = 1.5 V (max)
- Pin and function compatible with the 74 series (74AC/HC/F/ALS/LS etc.) 374 type.

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damage to property.

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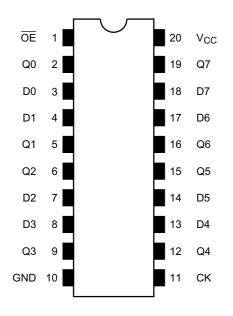
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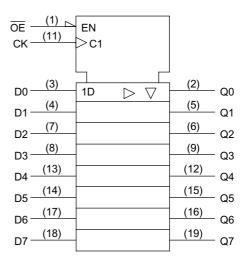
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Pin Assignment (top view)



IEC Logic Symbol



Truth Table

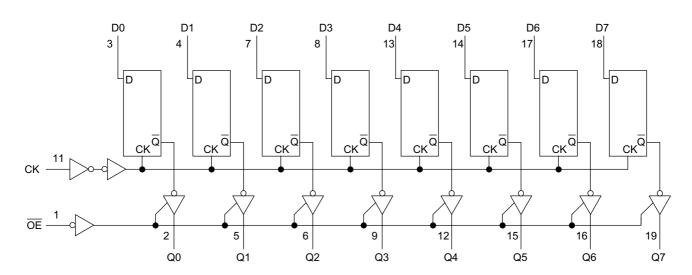
	Outputs		
ŌĒ	CK	Outputs	
Н	Х	Х	Z
L	\rightarrow	Х	Q _n
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Q_n: No change

System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	٧
DC output voltage	Vout	-0.5~7.0 (Note1)	V
DC output voltage	VOU1	-0.5~V _{CC} + 0.5 (Note2)	V
Input diode current	I _{IK}	-20	mA
Output diode current	I _{OK}	±20 (Note3)	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	I _{CC}	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	-65~150	°C

Note1: Output in off-state

Note2: High or low state. IOUT absolute maximum rating must be observed.

Note3: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	4.5~5.5	٧
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~5.5 (Note4)	V
Output voltage		0~V _{CC} (Note5)	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~20	ns/V

Note4: Output in off-state Note5: High or low state



Electrical Characteristics

DC Characteristics

Characteristics		Symbol Test C		Condition		Ta = 25°C			Ta = -40~85°C		Unit
		Syllibol	Symbol Test Com		V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
Input voltage	High level	V _{IH}		_	4.5~5.5	2.0	_	_	2.0	_	V
input voltage	Low level	V _{IL}		_	4.5~5.5	_	_	8.0	_	0.8	V
	High level	V _{OH}	$V_{IN} = V_{IH}$	$I_{OH} = -50 \mu A$	4.4	4.5	_	4.4	_	_	V
Output voltage	i ligit level	VOH	or V _{IL}	$I_{OH} = -8 \text{ mA}$	3.94	_	_	3.80	_	_	
Output voltage	High level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 50 \mu A$	_	0	0.1	_	0.1	0.1	
				I _{OL} = 8 mA	_	_	0.36	_	0.44	0.44	
3-state output off-state current I _{OZ} "" "		$V_{IN} = V_{IH}$ $V_{OUT} = V_{OUT}$	or V _{IL} _{CC} or GND	5.5	_	_	±0.25	_	±2.50	μА	
Input leakage cu	ırrent	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5	_	_	±0.1	_	±1.0	μΑ
		I _{CC}	$V_{IN} = V_{CC}$ or GND		5.5	_	_	4.0	_	40.0	μΑ
Quiescent supply current		I _{CCT}	Per input: $V_{IN} = 3.4 \text{ V}$ Other input: V_{CC} or GND		5.5	_	_	1.35	_	1.50	mA
Output leakage	current	I _{OPD}	V _{OUT} = 5.5 V		0	_	_	0.5	_	5.0	μΑ

Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Sumbol Test Condition		Ta = 25°C		Ta = -40~85°C	Unit
Characteristics	Characteristics Symbol Test Condition		V _{CC} (V)	Тур.	Limit	Limit	Offic
Minimum pulse width (CK)	t _{w (H)} t _{w (L)}	_	5.0 ± 0.5	_	6.5	8.5	ns
Minimum set-up time	t _s	_	5.0 ± 0.5	_	2.5	2.5	ns
Minimum hold time	t _h	_	5.0 ± 0.5	_	2.5	2.5	ns



AC Electrical Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol Test Condition				Ta = 25°C			Ta = -4	Unit	
Characteristics	Symbol	Test Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Oill
Propagation delay time	t _{pLH}		5.0 ± 0.5	15	_	4.1	9.4	1.0	10.5	ns
(CK-Q)	t _{pHL}	_	3.0 ± 0.3	50		5.6	10.4	1.0	11.5	10
3-state output enable time	t _{pZL}	$R_L = 1 \text{ k}\Omega$	5.0 ± 0.5	15		6.5	10.2	1.0	11.5	ns
3-state output enable time	tpZH	N 1 N22	3.0 ± 0.3	50		7.3	11.2	1.0	12.5	115
3-state output disable time tpH	t _{pLZ}	$R_L = 1 \text{ k}\Omega$	5.0 ± 0.5	15		7.0	11.2	1.0	12.0	
	t _{pHZ} f _{max}			50	90	140		80		ns
Maximum clock frequency	f _{max}		5.0 ± 0.5	50	85	130		75	_	MHz
Output to output skew	t _{osLH} t _{osHL}	(Note6)	5.0 ± 0.5	50		_	1.0	_	1.0	ns
Input capacitance	C _{IN}	_		_	4	10	_	10	pF	
Output capacitance	C _{OUT}	_			9			_	pF	
Power dissipation capacitance	C _{PD}			(Note7)		25		_	_	pF

Note6: Parameter guaranteed by design.

 $t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|$

Note7: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per F/F)$

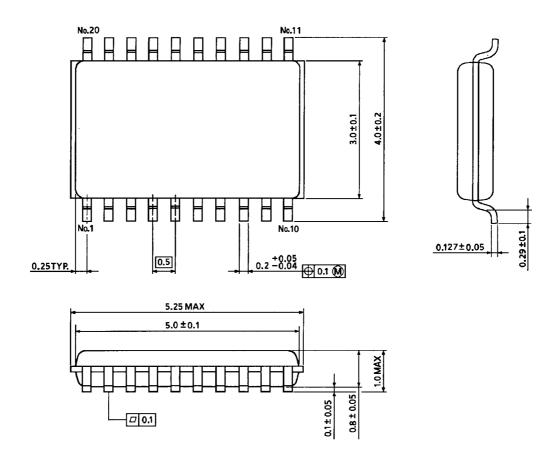
And the total CPD when n pcs. of latch operate can be gained by the following equation:

C_{PD} (total) = 14 + 11 · n

Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition	Ta = 25°C		25°C	Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	1.1	1.5	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-1.1	-1.5	V
Minimum high level dynamic input voltage V _{IH}	V _{IHD}	C _L = 50 pF	5.0	_	2.0	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0	_	0.8	V

Package Dimensions



Weight: 0.03 g (typ.)